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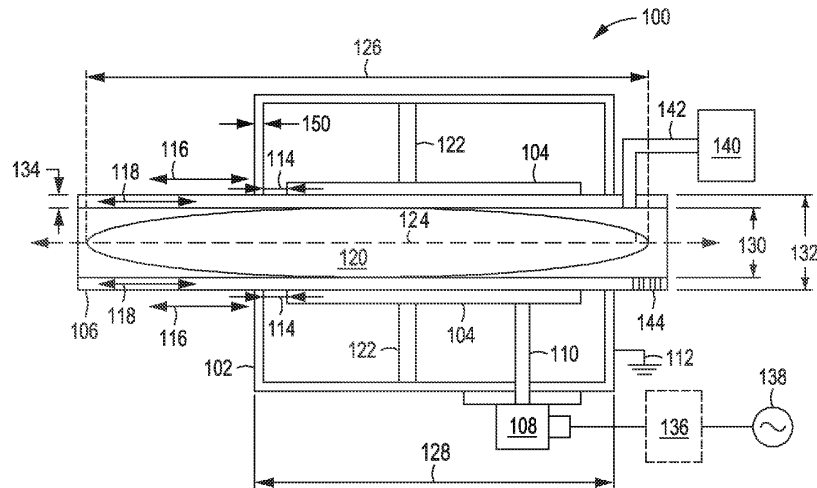


FIG. 1

(57) Abstract: Apparatus provide plasma to a processing volume of a chamber. The Apparatus may comprise a plurality of plasma sources, each with at least a dielectric tube inlet which is at least partially surrounded by a conductive tube which is configured to be connected to RF power to generate plasma and a gas inlet positioned opposite the dielectric tube inlet for a process gas and a dielectric tube directly connected to each of the plurality of plasma sources where the dielectric tube is configured to at least partially contain plasma generated by the plurality of plasma sources and to release radicals generated in the plasma via holes in the dielectric tube.

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